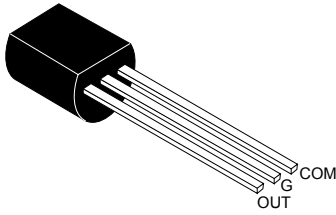
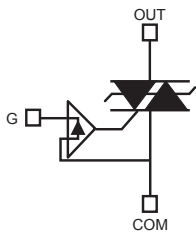


0.8 A - 600 V overvoltage protected AC switch (ACS)



TO-92



COM Common drive reference to connect to the mains
 OUT Output to connect to the load.
 G Gate input to connect to the controller through gate resistor

Features

- Enables equipment to meet IEC 61000-4-5 surge with overvoltage crowbar technology
- High noise immunity against static dV/dt and IEC 61000-4-4 burst
- Needs no external protection snubber or varistor
- Reduces component count by up to 80% and Interfaces directly with the micro-controller
- Common package tab connection supports connection of several alternating current switches on the same cooling pad
- V_{CL} gives headroom before clamping then crowbar action

Applications

- Alternating current on/off static switching in appliances and industrial control systems
- Driving low power high inductive or resistive loads like:
 - relay, valve, solenoid, dispenser
 - pump, fan, low power motor, door lock, air flow dumper
 - lamp

Description

The BT131 belongs to the AC switch range. This high performance switch can control a load of up to 0.8 A.

This device switch includes an overvoltage crowbar structure to absorb the inductive turn-off energy, and a gate level shifter driver to separate the digital controller from the main switch. It is triggered with a negative gate current flowing out of the gate pin.

Product status link

[BT131](#)

Product summary

$I_{T(RMS)}$	0.8 A
V_{DRM}, V_{RRM}	600 V
I_{GT}	10 mA

1 Characteristics

Table 1. Absolute maximum ratings ($T_{amb} = 25\text{ °C}$, unless otherwise specified)

Symbol	Parameter	Value	Unit	
$I_{T(RMS)}$	On-state rms current (full sine wave), $S = 5\text{ cm}^2$	$T_{amb} = 64\text{ °C}$	0.45	A
		$T_{lead} = 76\text{ °C}$	0.8	
I_{TSM}	Non repetitive surge peak on-state current T_j initial = 25 °C , (full cycle sine wave)	$t_p = 20\text{ ms}$	13	A
		$t_p = 16.7\text{ ms}$	13.7	
I^2t	I^2t for fuse selection	$t_p = 10\text{ ms}$	1.1	A^2s
di/dt	Critical rate of rise on-state current $I_G = 2 \times I_{GT}$, $tr \leq 100\text{ ns}$	$f = 120\text{ Hz}$, $T_j = 125\text{ °C}$	100	$\text{A}/\mu\text{s}$
$V_{PP}^{(1)}$	Non repetitive line peak pulse voltage		2	kV
$P_{G(AV)}$	Average gate power dissipation	$T_j = 125\text{ °C}$	0.1	W
V_{GM}	Peak positive gate voltage	$T_j = 125\text{ °C}$	10	V
I_{GM}	Peak gate current ($t_p = 20\text{ }\mu\text{s}$)	$T_j = 125\text{ °C}$	1	A
T_{stg}	Storage temperature range		-40 to +150	$^{\circ}\text{C}$
T_j	Operating junction temperature range		-30 to +125	$^{\circ}\text{C}$

1. according to test described by standard IEC 61000-4-5, see Figure 15. Overvoltage ruggedness test circuit for resistive and inductive loads, $T_{amb} = 25\text{ °C}$ (conditions equivalent to IEC 61000-4-5 standard) for conditions

Table 2. Electrical characteristics ($T_j = 25\text{ °C}$, unless otherwise specified)

Symbol	Test conditions	Quadrant	Value	Unit	
$I_{GT}^{(1)}$	$V_{OUT} = 12\text{ V}$, $R_L = 33\text{ }\Omega$	II - III	Max.	10	mA
V_{GT}			Max.	1.0	V
V_{GD}	$V_{OUT} = V_{DRM}$, $R_L = 3.3\text{ k}\Omega$, $T_j = 125\text{ °C}$	II - III	Min.	0.15	V
I_H	$I_{OUT} = 100\text{ mA}$		Max.	10	mA
I_L	$I_G = 1.2 \times I_{GT}$		Max.	25	mA
dV/dt	$V_{OUT} = 402\text{ V}$, gate open, $T_j = 125\text{ °C}$		Min.	2000	$\text{V}/\mu\text{s}$
$(di/dt)_c$	Without snubber ($15\text{ V}/\mu\text{s}$), $T_j = 125\text{ °C}$, turn-off time $\leq 20\text{ ms}$		Min.	2	A/ms
V_{CL}	$I_{CL} = 0.1\text{ mA}$, $t_p = 1\text{ ms}$		Min.	650	V

1. Minimum I_{GT} is guaranteed at 10% of I_{GT} max.

Table 3. Static electrical characteristics

Symbol	Test conditions	Value	Unit
$V_{TM}^{(1)}$	$I_{TM} = 1.1\text{ A}$, $t_p = 500\text{ }\mu\text{s}$	$T_j = 25\text{ °C}$	Max. 1.3 V
$V_{T0}^{(1)}$	Threshold voltage	$T_j = 125\text{ °C}$	Max. 0.85 V
$R_d^{(1)}$	Dynamic resistance	$T_j = 125\text{ °C}$	Max. 300 m Ω
I_{DRM} I_{RRM}	$V_{OUT} = V_{DRM}/V_{RRM}$	$T_j = 25\text{ °C}$	Max. 2 μA
		$T_j = 125\text{ °C}$	0.2 mA

1.1 Characteristics (curves)

Figure 1. Maximum power dissipation versus rms on-state current

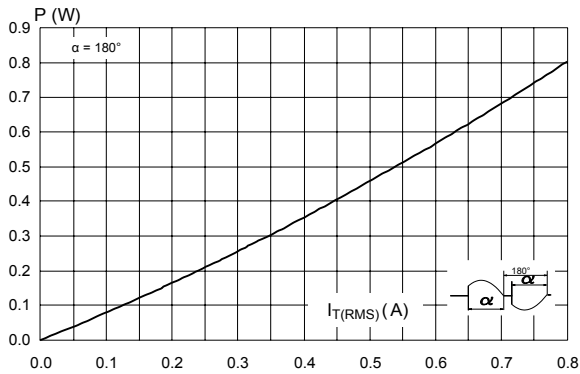


Figure 2. On-state rms current versus ambient temperature

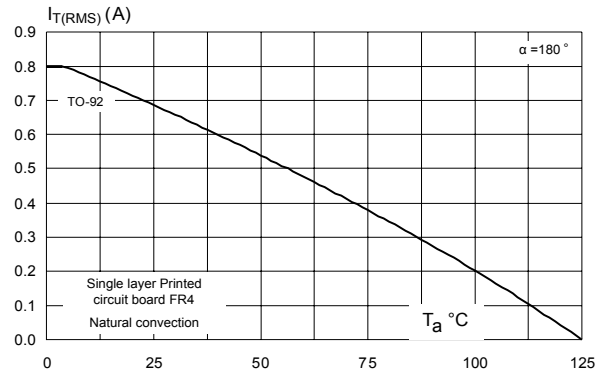


Figure 3. Relative variation of thermal impedance junction to ambient versus pulse duration

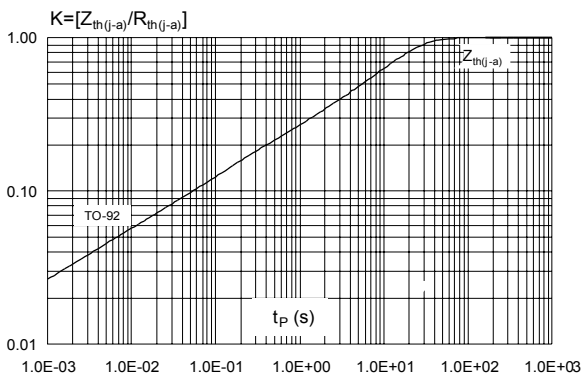


Figure 4. Relative variation of holding and latching current versus junction temperature

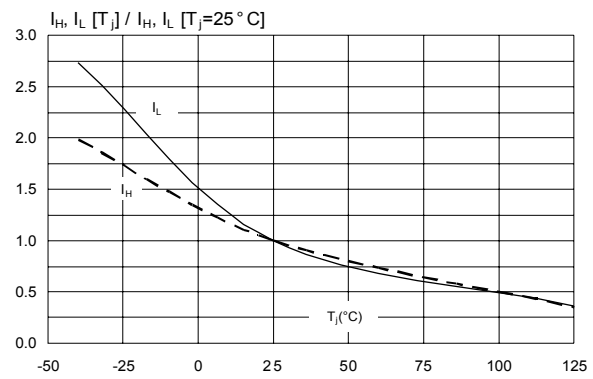


Figure 5. Relative variation of I_GT and V_GT versus junction temperature

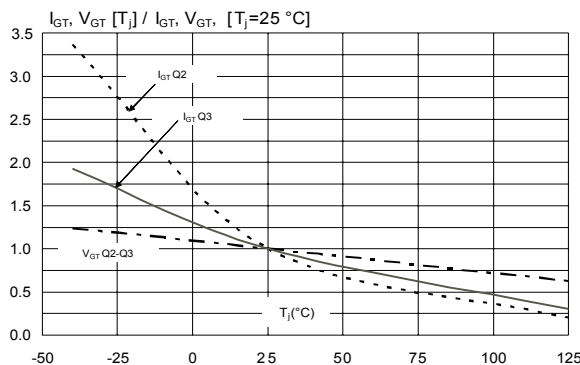
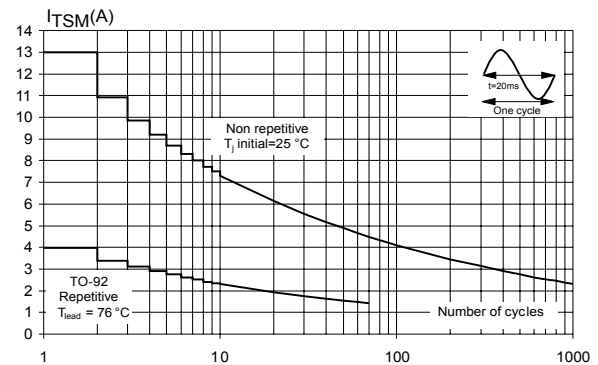


Figure 6. Surge peak on-state current versus number of cycles



2.1 TO-92 package information

- Lead free plating + halogen-free molding resin

Figure 7. TO-92 package outline

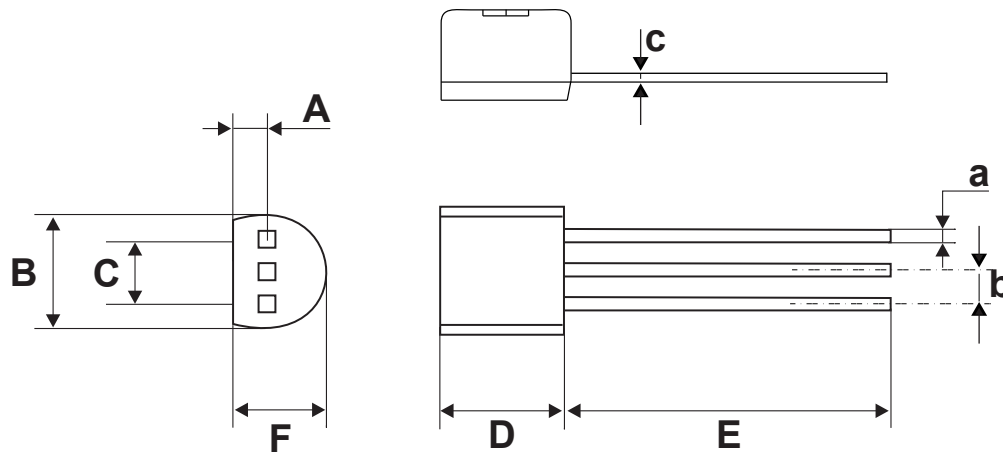


Table 4. TO-92 package mechanical data

Ref.	Dimensions					
	Millimeters			Inches ⁽¹⁾		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A		1.35			0.0531	
B			4.70			0.1850
C		2.54			0.1000	
D	4.40			0.1732		
E	12.70			0.5000		
F			3.70			0.1457
a			0.50			0.0197
b		1.27			0.500	
c			0.48			0.0189

1. Inches dimensions given for information

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